

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

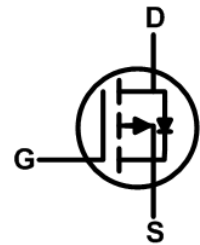
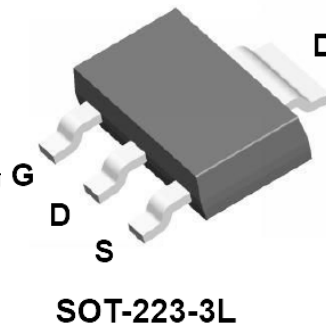

Product Summary

BVDSS	RDS(on)	ID
-60V	70mΩ	-10A

Description

The XXW10P06K is the high cell density trenched P-ch MOSFETs, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The XXW10P06K meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

SOT223 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-10	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-6.3	A
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3.3	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-2.7	A
I_{DM}	Pulsed Drain Current ²	-26	A
EAS	Single Pulse Avalanche Energy ³	29.8	mJ
I_{AS}	Avalanche Current	24.4	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	31.3	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4	$^\circ\text{C/W}$

P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.023	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-10A$	---	70	90	$m\Omega$
		$V_{GS}=-4.5V, I_D=-5A$	---	85	115	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.65	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-4A$	---	8.7	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	15	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-12V, V_{GS}=-4.5V, I_D=-6A$	---	11.8	---	nC
Q_{gs}	Gate-Source Charge		---	1.9	---	
Q_{gd}	Gate-Drain Charge		---	6.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-1A$	---	8.8	---	ns
T_r	Rise Time		---	19.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	47.2	---	
T_f	Fall Time		---	9.6	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	---	1080	---	pF
C_{oss}	Output Capacitance		---	73	---	
C_{rss}	Reverse Transfer Capacitance		---	50	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-10	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-20	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3. The EAS data shows Max. rating. The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-24.4A$

4. The power dissipation is limited by 150°C junction temperature

5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

P-Channel Typical Characteristics

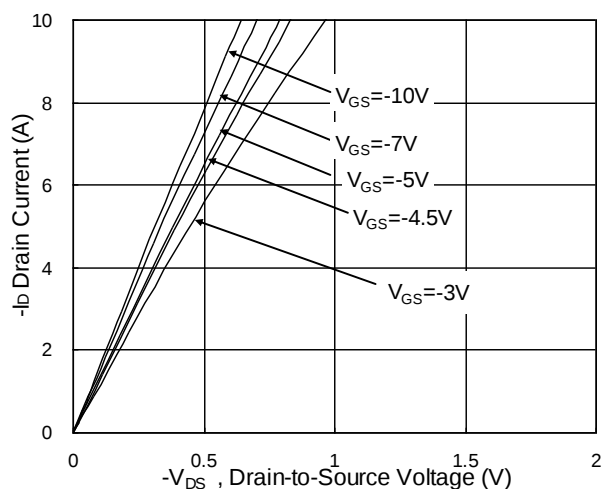


Fig.1 Typical Output Characteristics

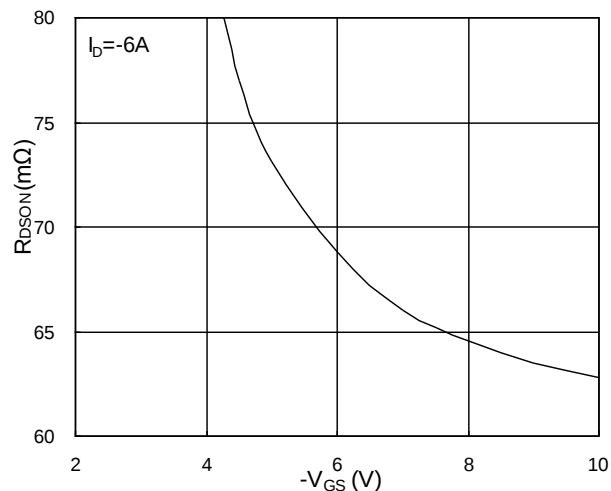


Fig.2 On-Resistance v.s Gate-Source

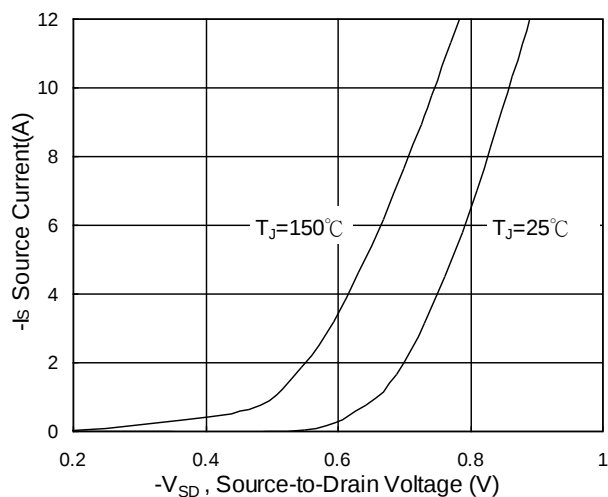


Fig.3 Forward Characteristics of Reverse

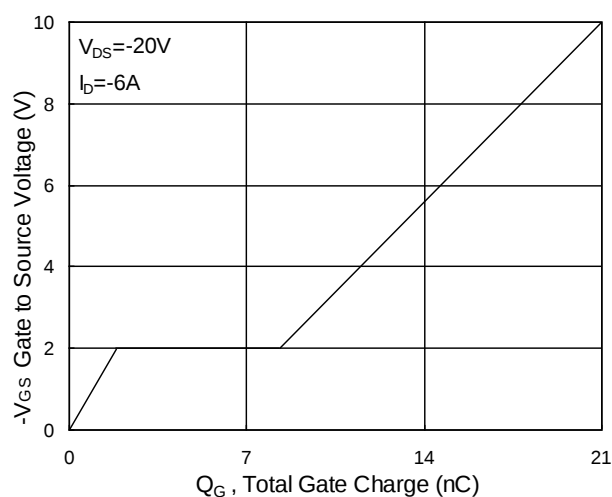


Fig.4 Gate-Charge Characteristics

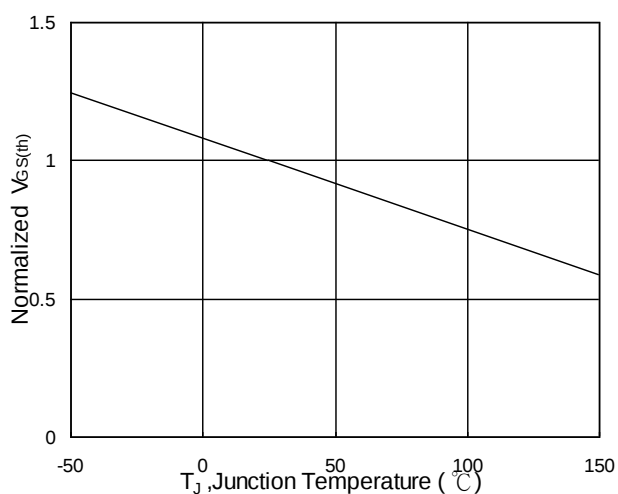


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

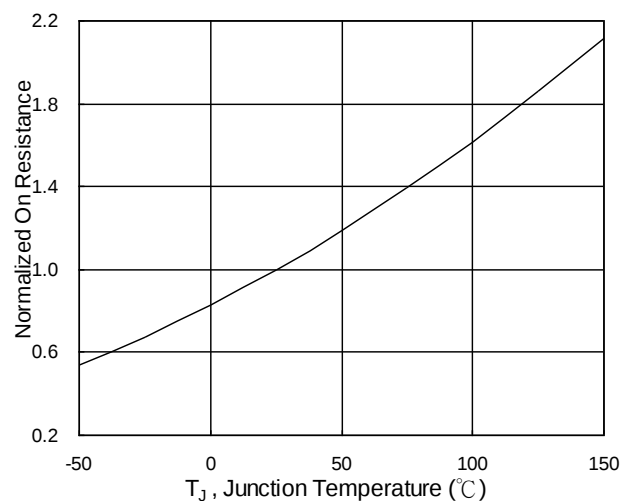


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

P-Ch 60V Fast Switching MOSFETs

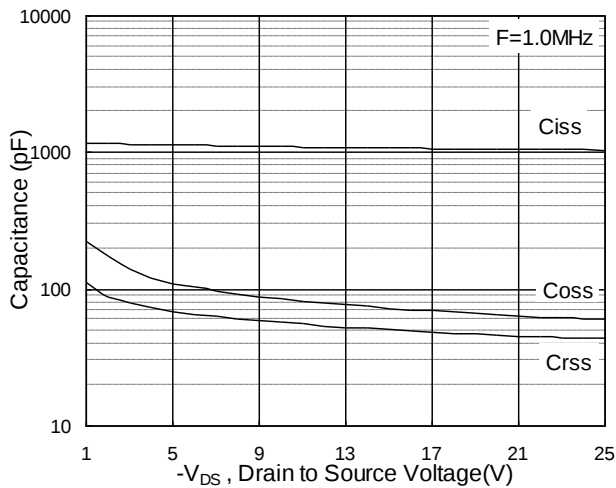


Fig.7 Capacitance

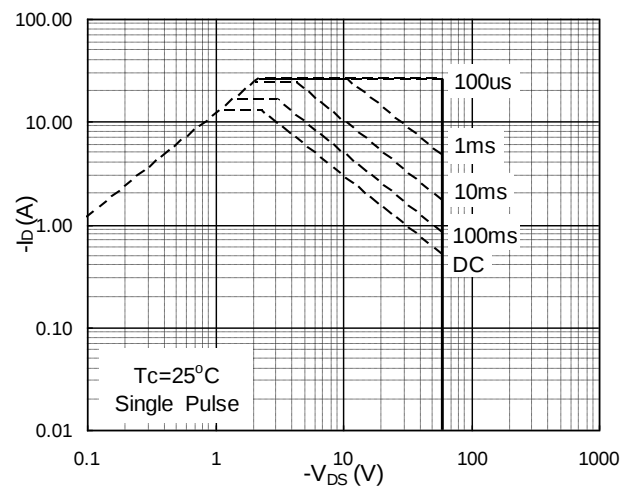


Fig.8 Safe Operating Area

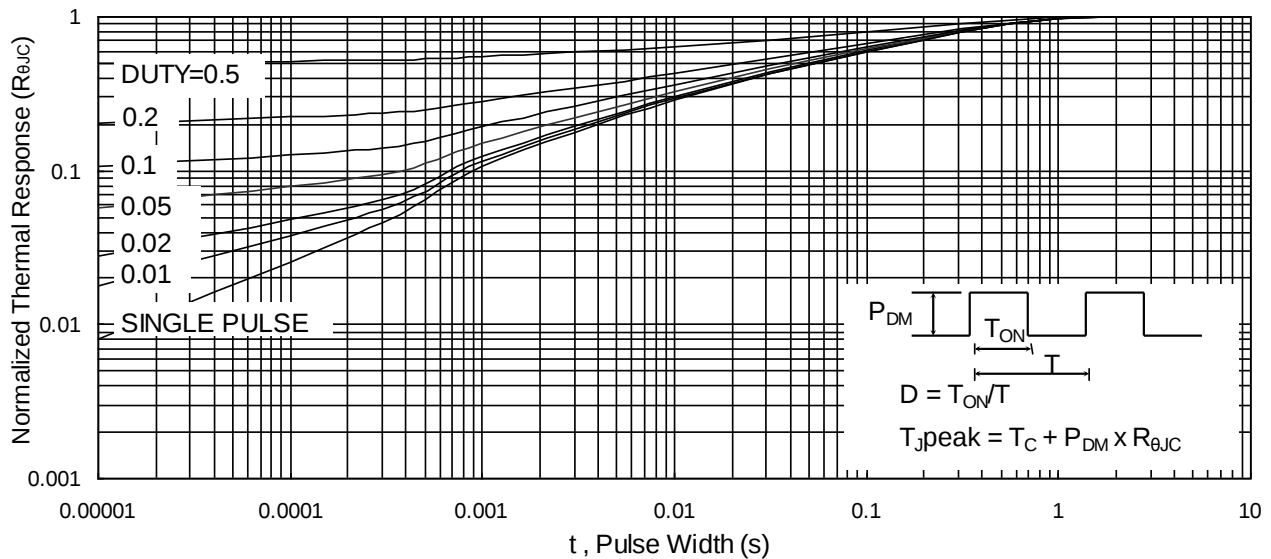


Fig.9 Normalized Maximum Transient Thermal Impedance

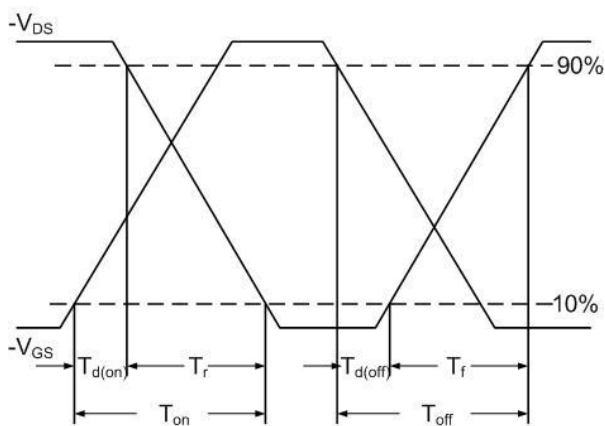


Fig.10 Switching Time Waveform

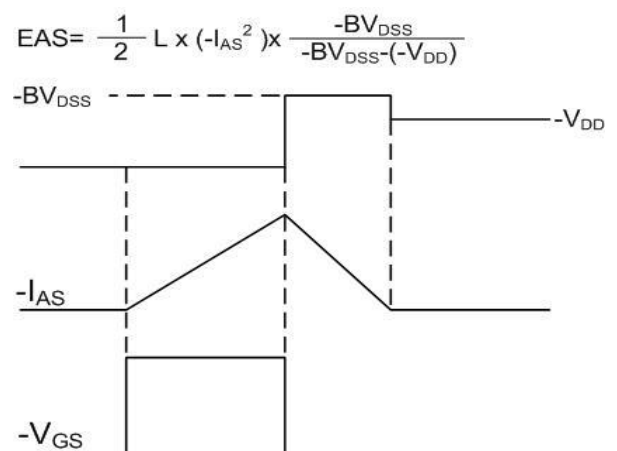
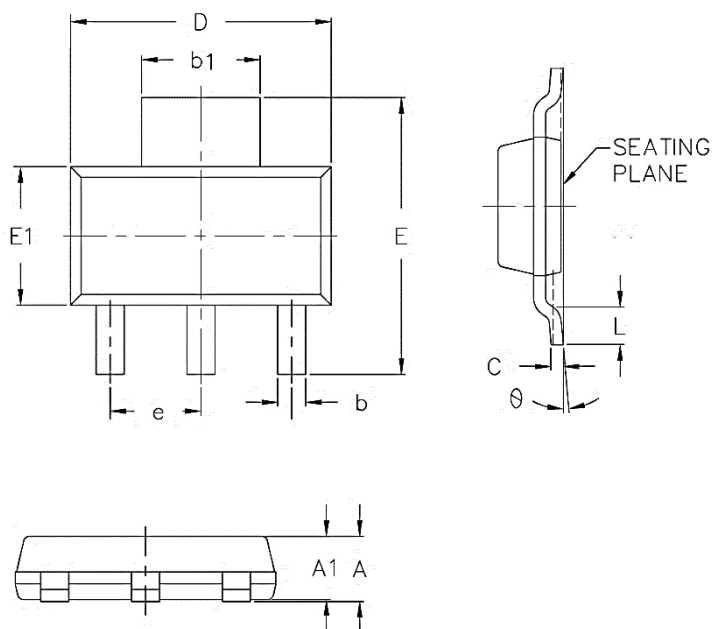


Fig.11 Unclamped Inductive Switching Waveform

Mechanical Dimensions for SOT-223-3L



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	-	1.80
A1	1.45	1.75
b	0.60	0.84
b1	2.90	3.10
C	0.23	0.35
D	6.20	6.70
E	6.70	7.30
E1	3.30	3.70
e	2.30BSC	
L	0.80	-
θ	0°	10°